sumably already governed by the elastic interaction of dislocations and defects and/or other dislocations, $\delta\sigma/\sigma$ shows no dependence on work hardening. It is not unreasonable to expect, then, that in sufficiently pure material the determination of $\delta\sigma/\sigma$ in an etch-pit experiment ($\epsilon_p \simeq 0$) would yield values of V^* considerably larger than found here. Hanafee and Radcliffe[30] have performed etch-pitting experiments on LiF deformed under pressure and find a V^* of about 4 V_a for both soft crystals and hardened, "doped" crystals. They suggest that dislocation motion in LiF is limited (at $\epsilon_p \simeq 0$) by the formation of interstitials by a climbing jog. However, similar experiments on LiF performed at this laboratory[31] give V^* approximately zero for both hard (irradiated) and soft crystals, a result in accord with the compression experiments.

[30] J. E. Hanafee and S. V. Radcliffe, J. Appl. Phys. **38,** 4284 (1967).

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[31] W. L. Haworth, L. A. Davis, and R. B. Gordon, J. Appl. Phys. **39,** 3818 (1968), this issue.